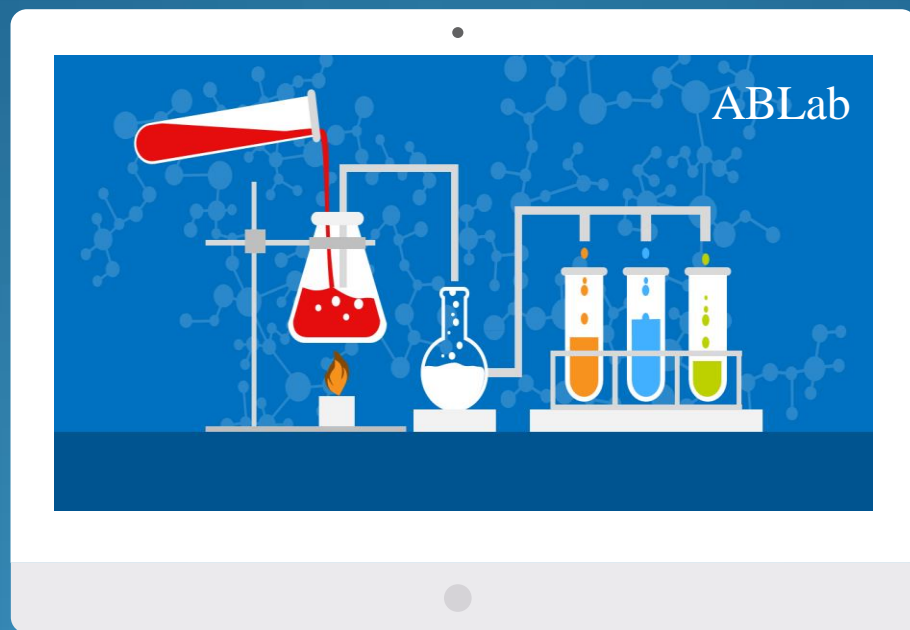


MoS₂/Graphene heterostructure to develop flexible electronics



五邑大学

Wuyi University



生物纳米材料应对当前健康挑战研讨会
Bionanomaterials for Current Health Challenges

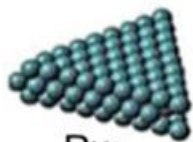
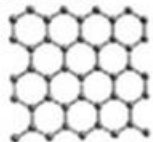


Ivan Babichuk
2023.09.05

2D materials

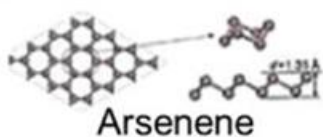
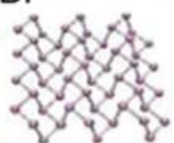
Elements

Graphene



Ru

BP

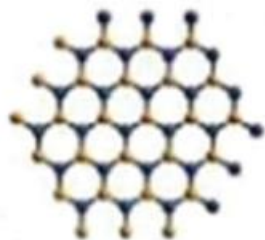


Arsenene

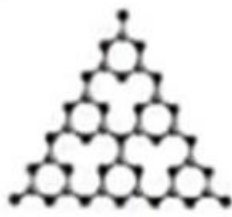


Silicene

Non-metallic compounds

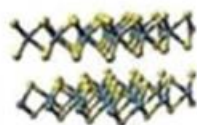


h-BN

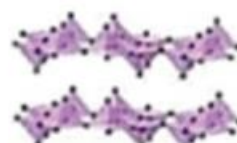


g-C₃N₄

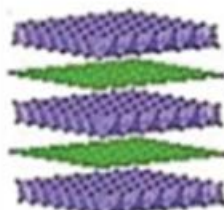
Metallic compounds



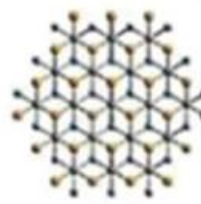
MoS₂



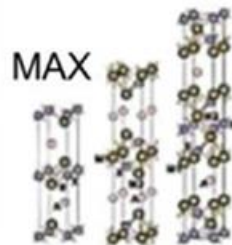
α -V₂O₅



LDHs



GaSe

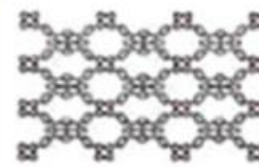


MAX

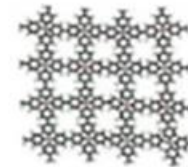


CrCl₃

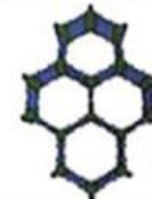
Organics



Zn - TCPP MOF

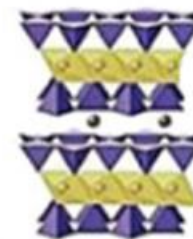


Polymer

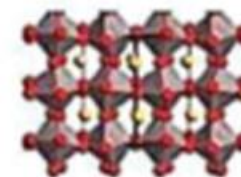


HHTP-DPB COF

Salts



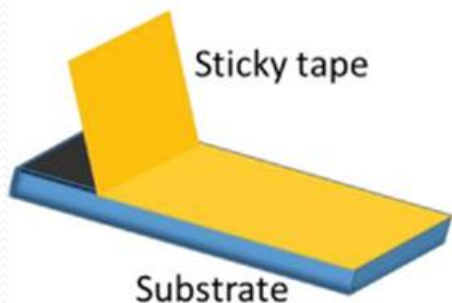
Clays



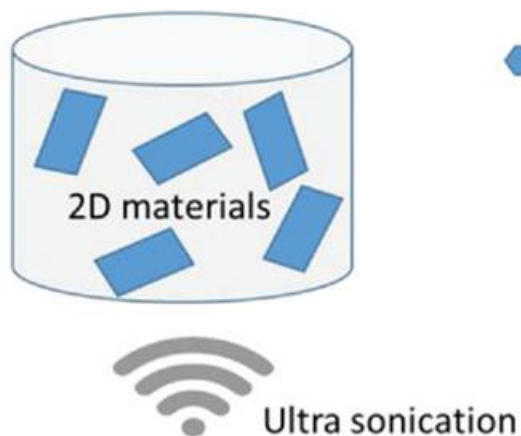
CaTiO₃

Synthesis of 2D Materials

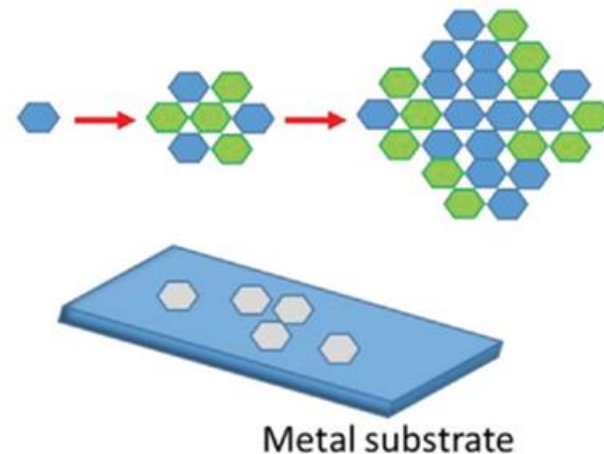
Mechanical cleavage



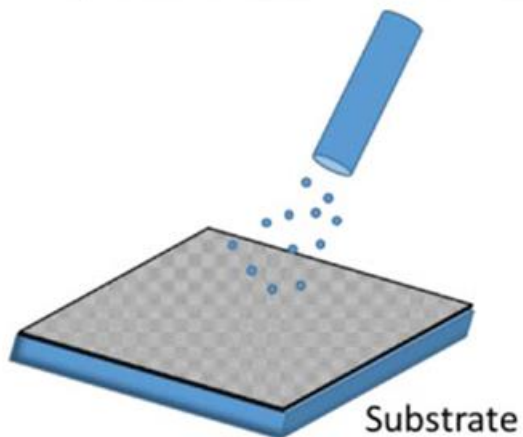
Liquid vapour exfoliation



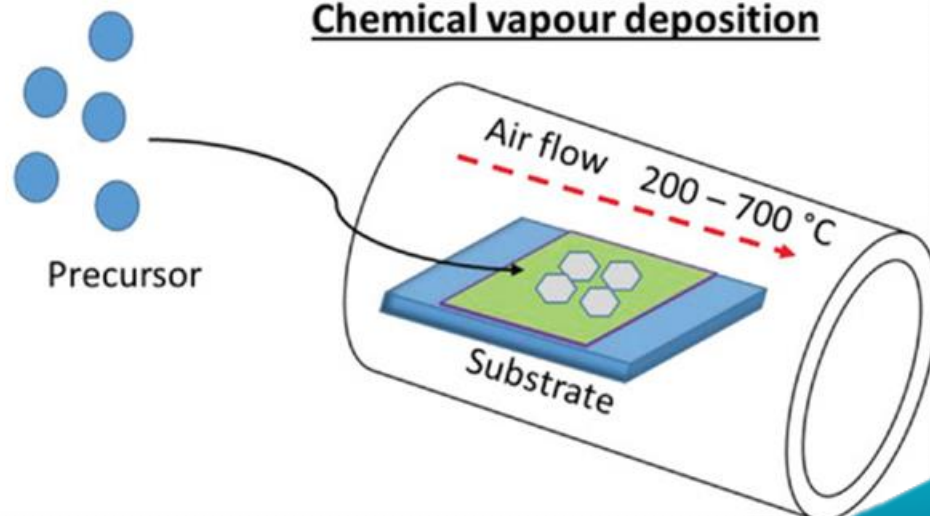
Chemical synthesis



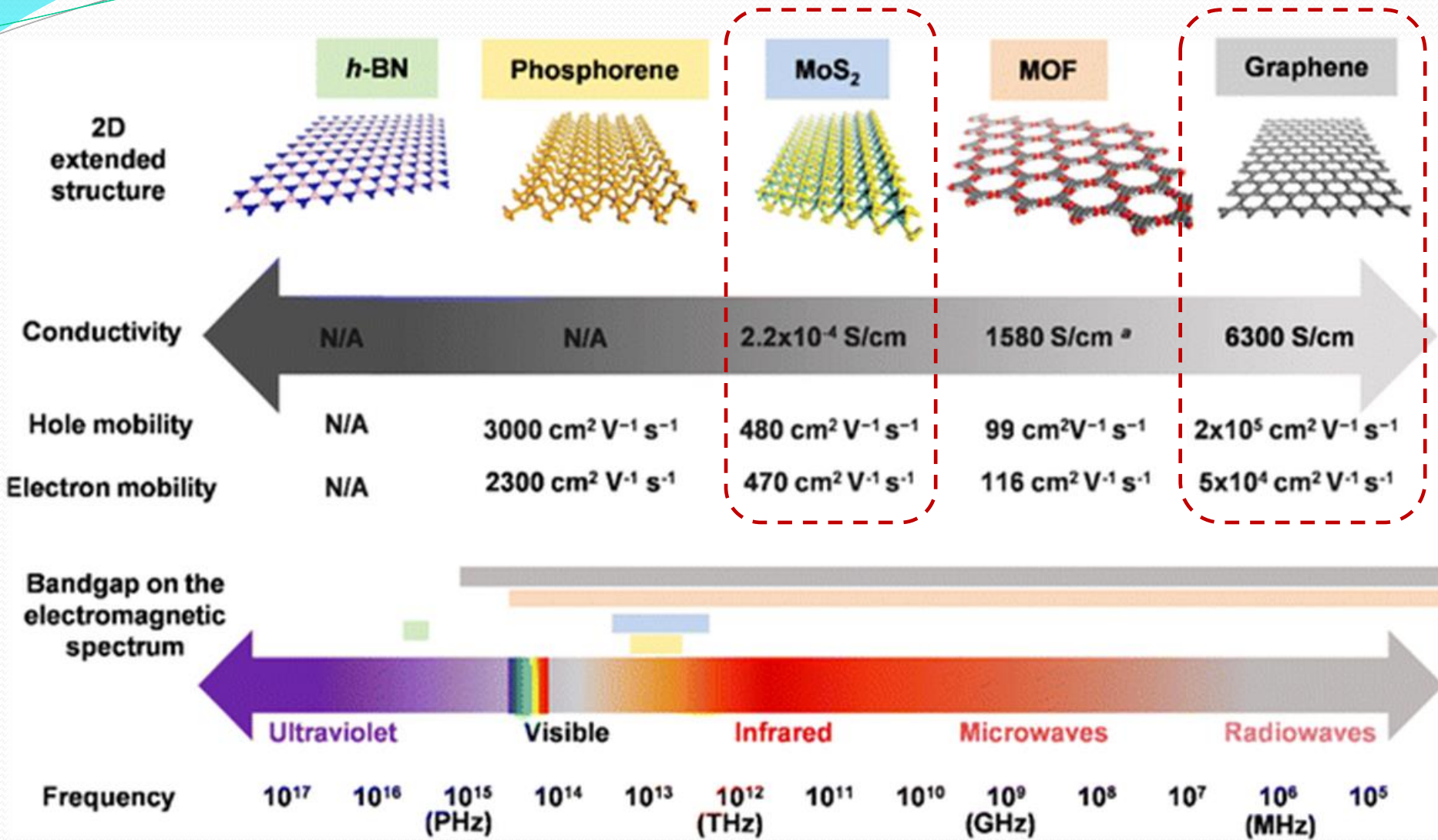
Physical vapour deposition



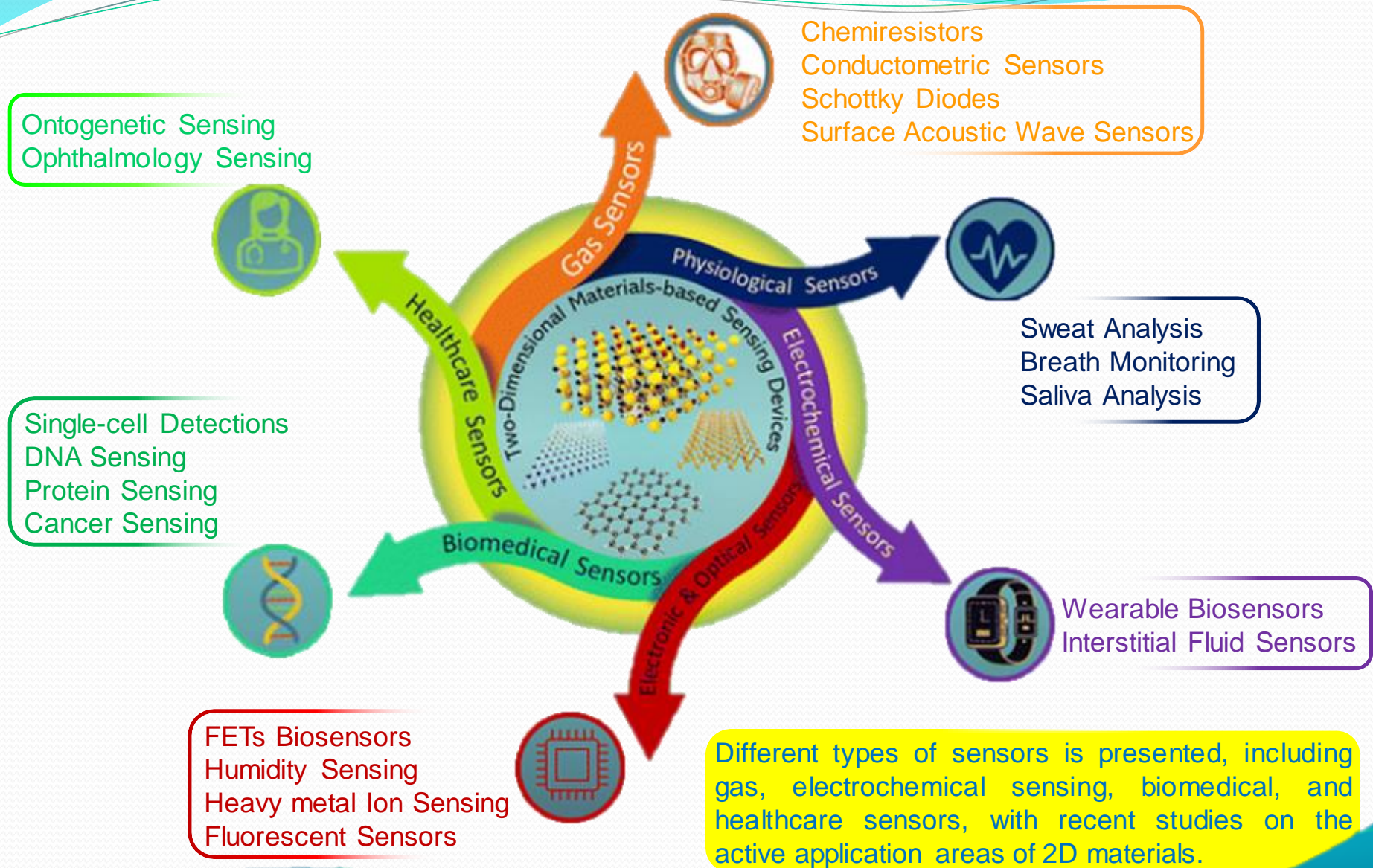
Chemical vapour deposition

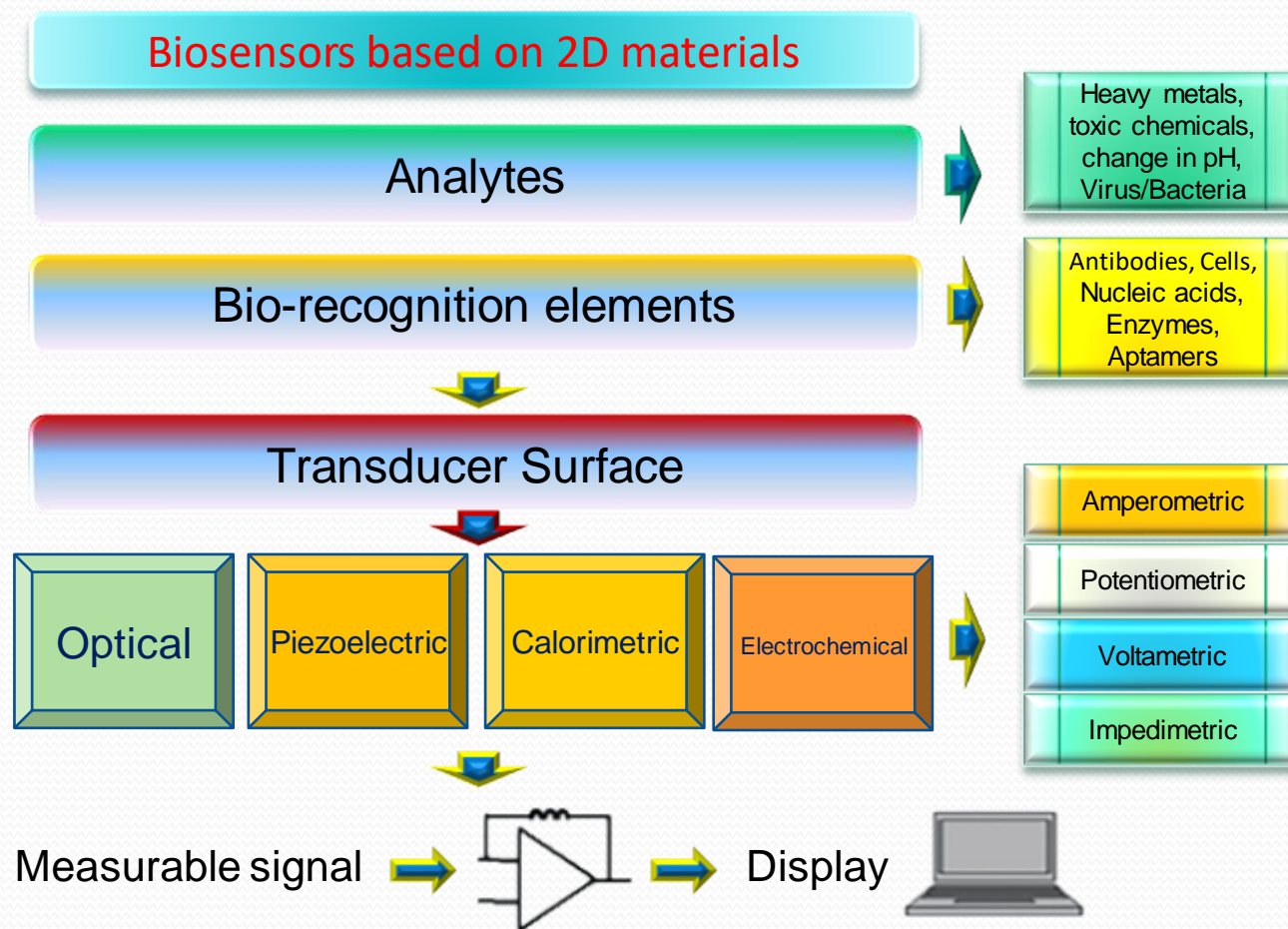


Why 2D materials for sensing?



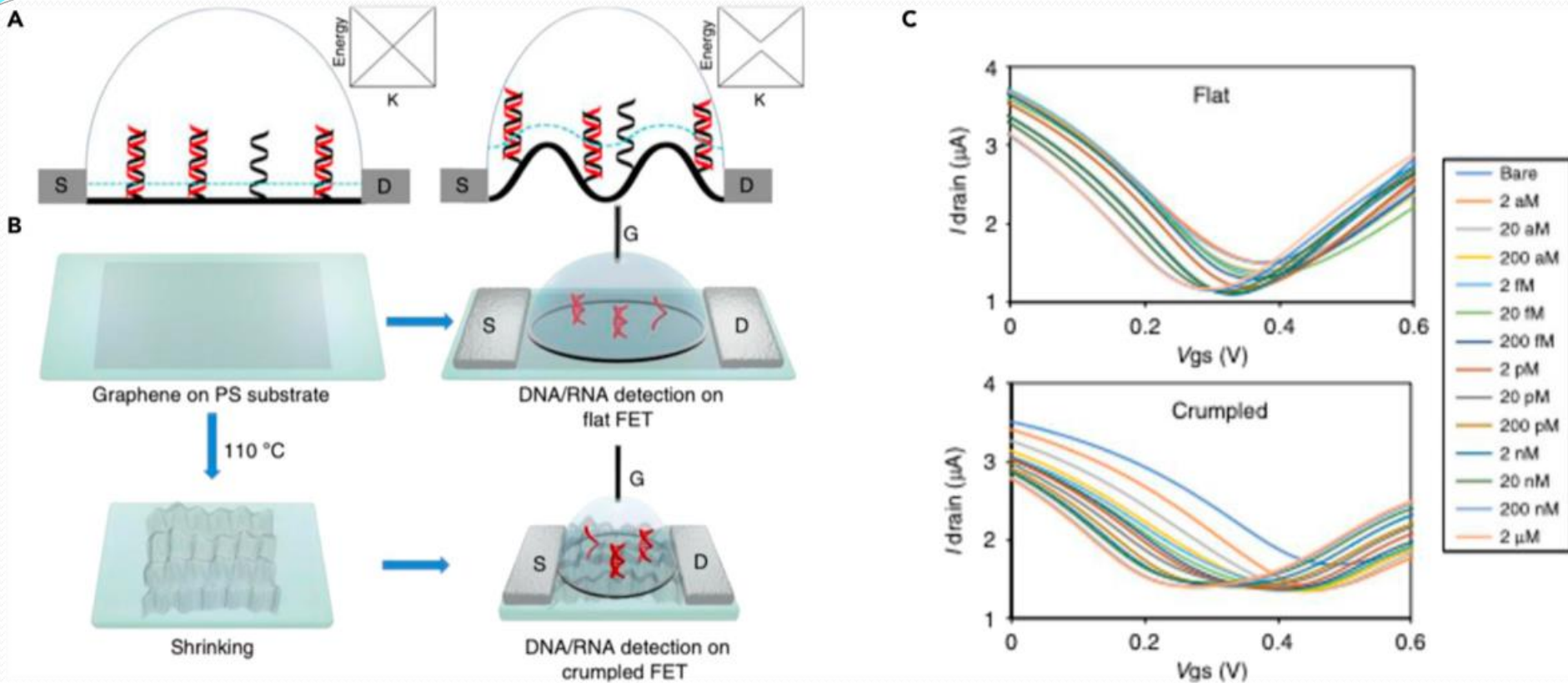
Highlights of 2D materials in various sensing devices



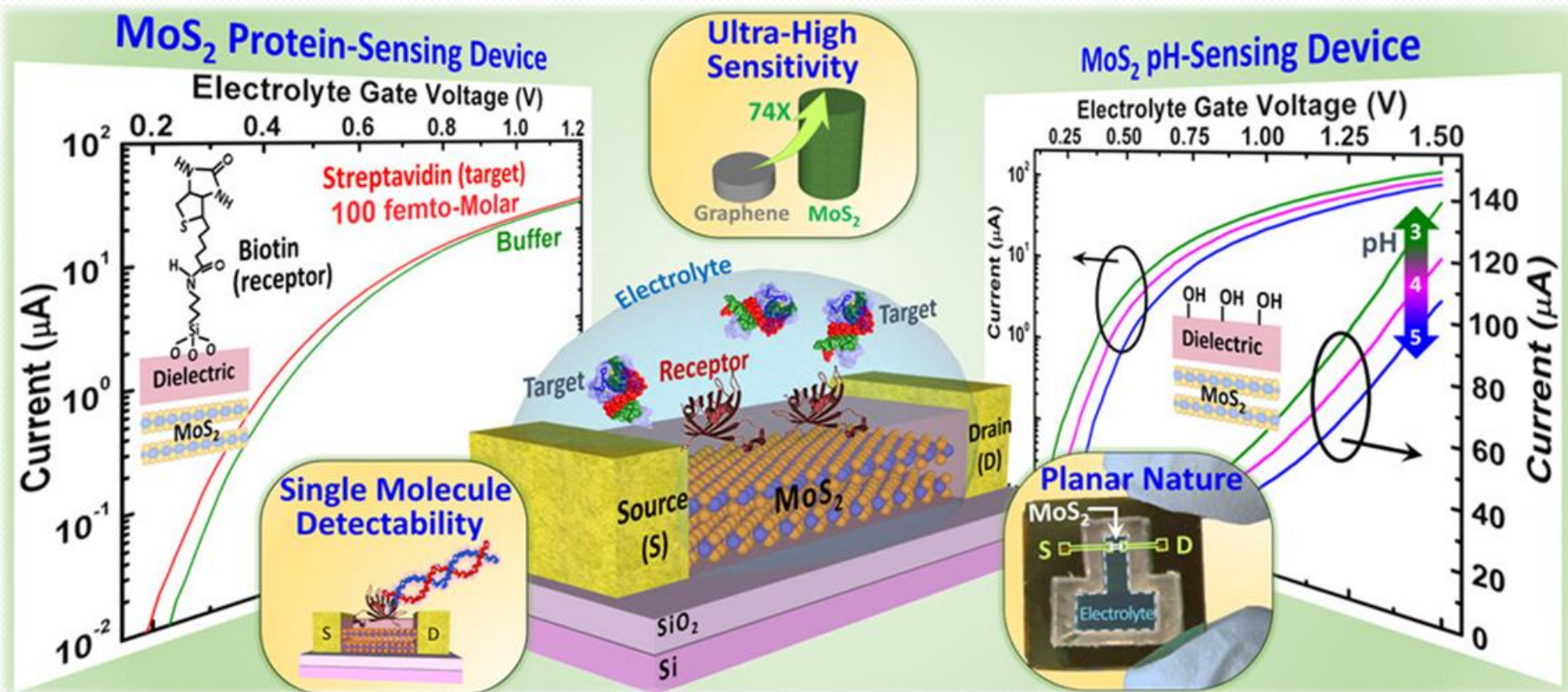


Biosensors based on 2D materials can be categorized, according to the usage of nanoscale components, into physical or chemical types. These are extremely sensitive in different practical applications over a diverse range of concentrations of analytes, including proteins, organic or inorganic molecules, viruses, and others. These sensors have three basic components transistors, resistors, and capacitors located in integrated circuits.

Graphene based biomolecule sensing

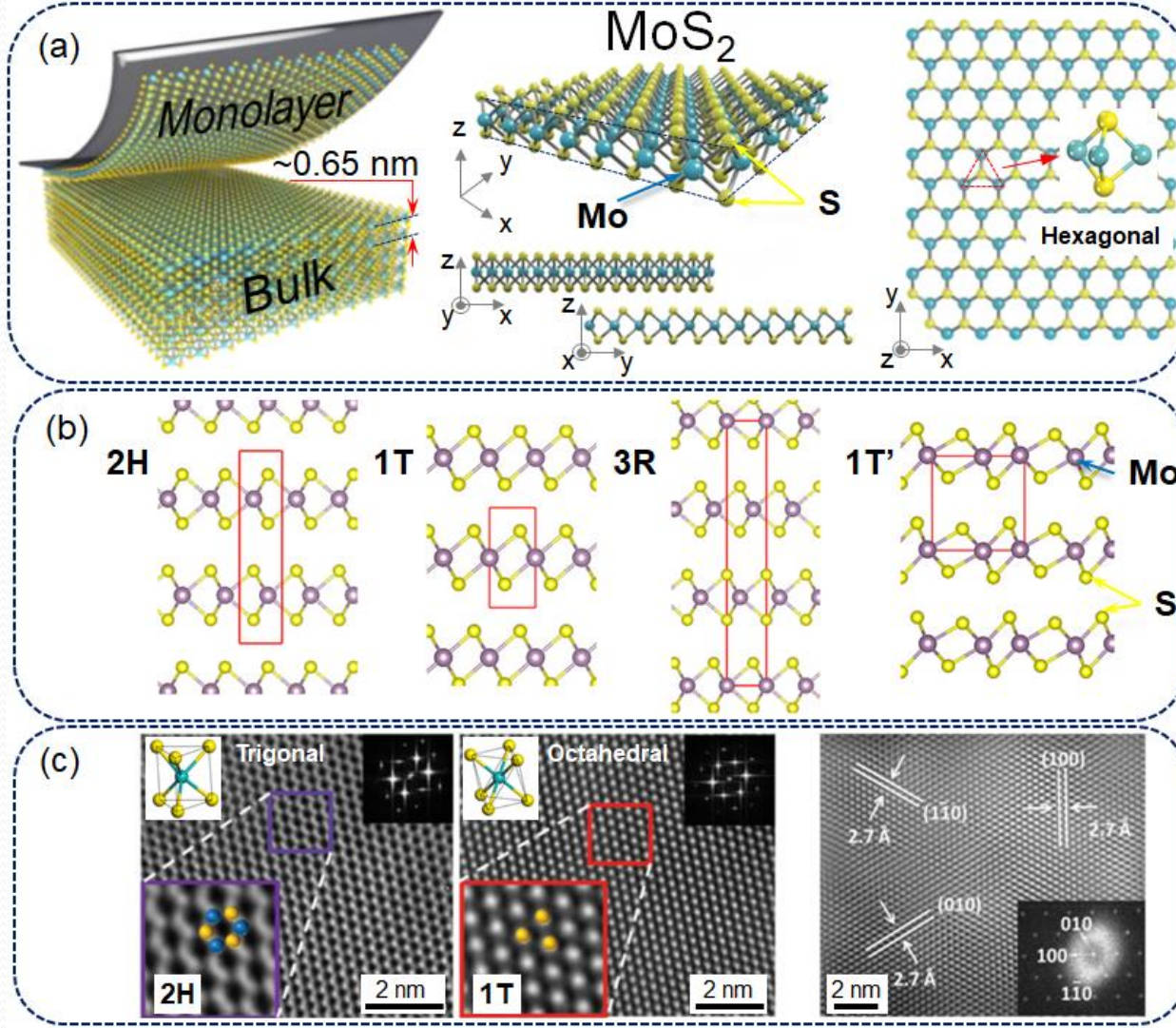


(A) Schematic diagrams of a flat (left) and a crumpled (right) graphene-based FET DNA sensor. DNA strands stay on the surface of graphene. The crumpled graphene is more sensitive to the negative charges of DNA than the flat version does. (B) Fabrication of graphene-based FET biosensors. The PS substrate is annealed to shrink and crumple the graphene. (C) IV characteristics of the flat and the crumpled graphene-based FET biosensors upon DNA absorption.



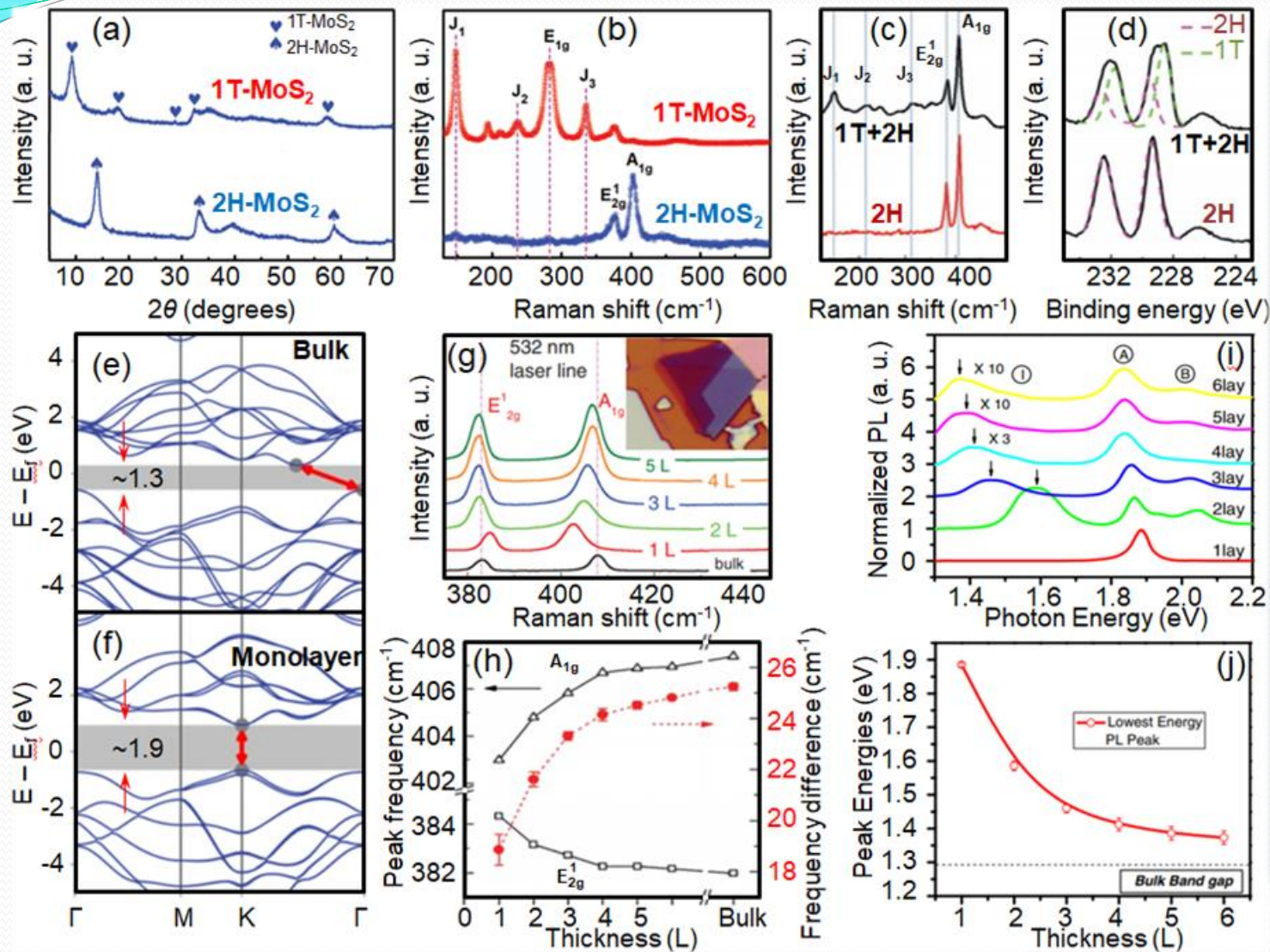
Schematic diagram of a MoS₂-based FET-based biosensor. For specifically capturing the target biomolecules, the dielectric layer above the MoS₂ channel is functionalized with receptors. The charged biomolecules after being captured induce a gating effect, modulating the device current. IV characteristics MoS₂-based FET biosensors. A critical problem of poor electric contact limits the development of more optimal MoS₂-based sensors. The problem stems from Fermi-level pinning in the interface between the MoS₂ and a metal.

The crystal structure of MoS₂

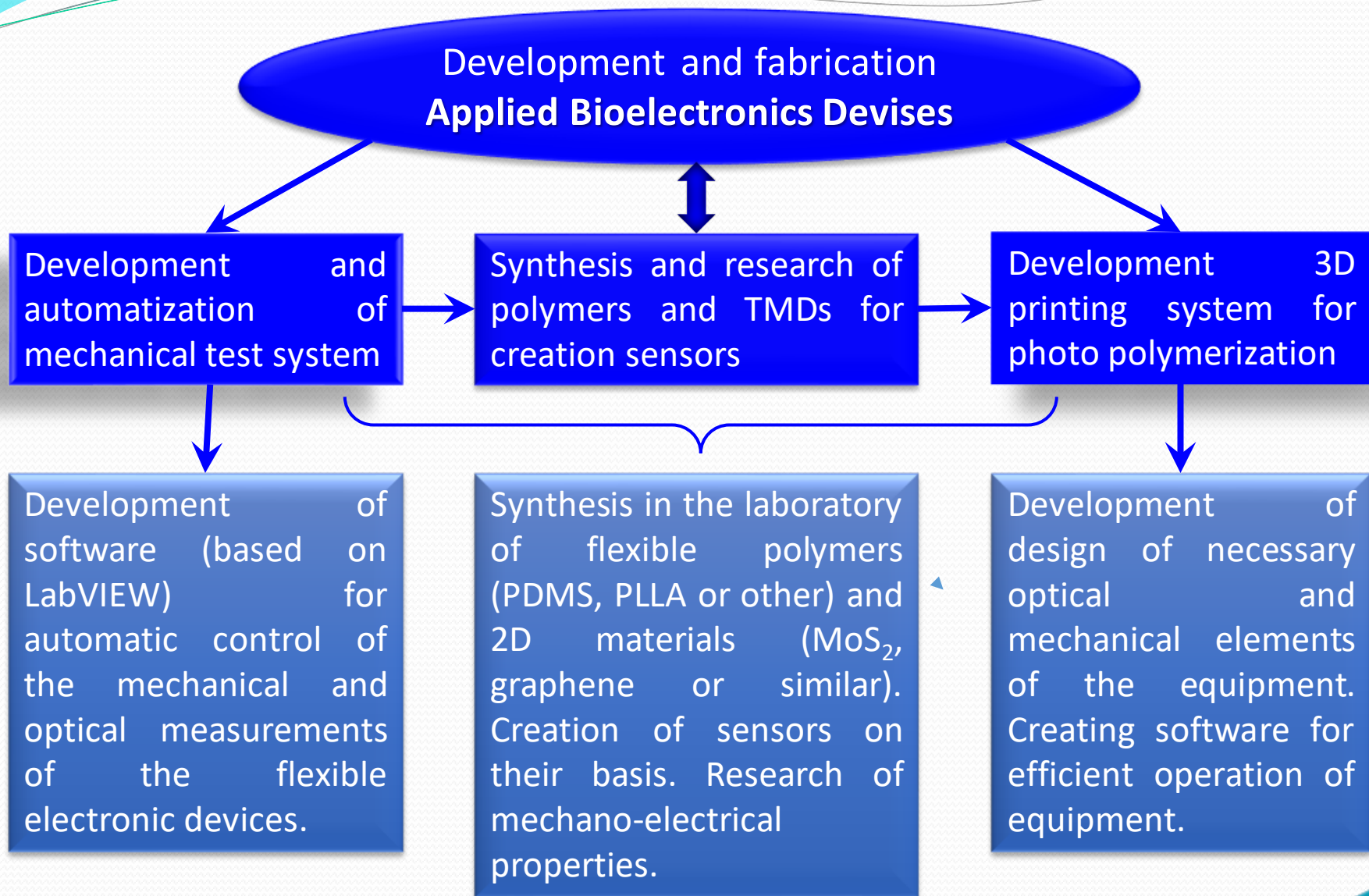


(A) Mechanical exfoliation is performed by successive peeling of adhesive tape from the surface of the bulk crystal. (B) This part figure shows the atomic configurations of MoS₂ in different phases (2H, 1T, 3R, and 1T'). (C) Atomic-resolution structural information and their corresponding fast Fourier transforms (FFTs) of trigonal prismatic (2H) and octahedral (1T) unit cells are shown thanks to the higher magnification HRTEM images of an exfoliated-MoS₂.

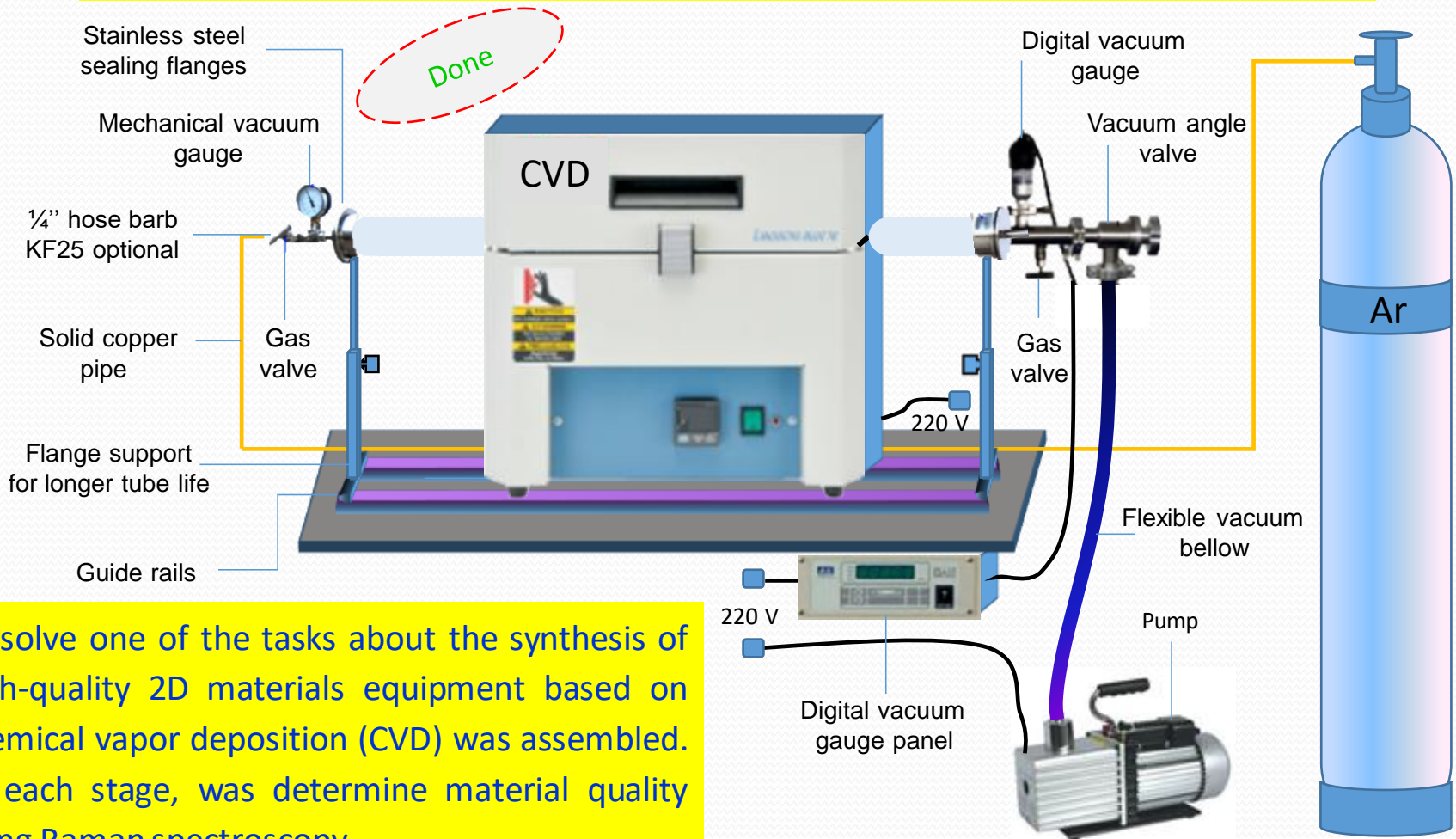
Characterization of the crystal structure of MoS₂



Phase and crystal structure of different polytypes MoS₂: (a) XRD patterns and Raman spectra (b) of the 1T-MoS₂ and 2H-MoS₂. The Raman and (d) XPS spectra show Mo 3d peak region of (1T+2H)-MoS₂ and 2H-MoS₂. The band structure diagram of bulk (e) and monolayer (f) MoS₂ shows the crossover from indirect to direct bandgap accompanied by a widening of the bandgap. (g) Raman characterizations of different thicknesses of sample MoS₂ using a 532 nm laser line. Inset: the optical image of the sample. The left and right dashed lines indicate the positions of the E_{2g}¹ and A_{1g} peaks in bulk MoS₂, respectively. (h) Frequencies of E_{2g}¹ and A_{1g} Raman modes. (i) Normalized PL spectra by the intensity of peak A of different thicknesses of sample MoS₂. (j) Band-gap energy of thin layers of MoS₂.



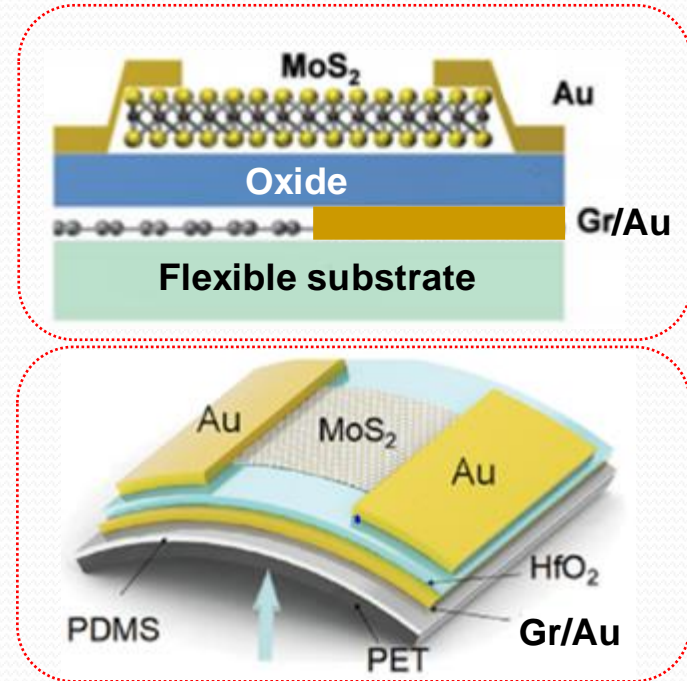
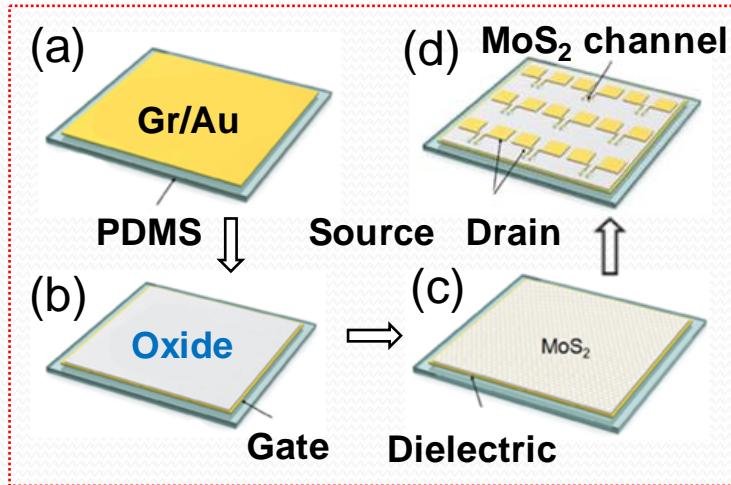
1. Collection of equipment for synthesis of 2D materials (molybdenum disulfide (MoS_2) or similar).



To solve one of the tasks about the synthesis of high-quality 2D materials equipment based on chemical vapor deposition (CVD) was assembled. At each stage, was determine material quality using Raman spectroscopy.

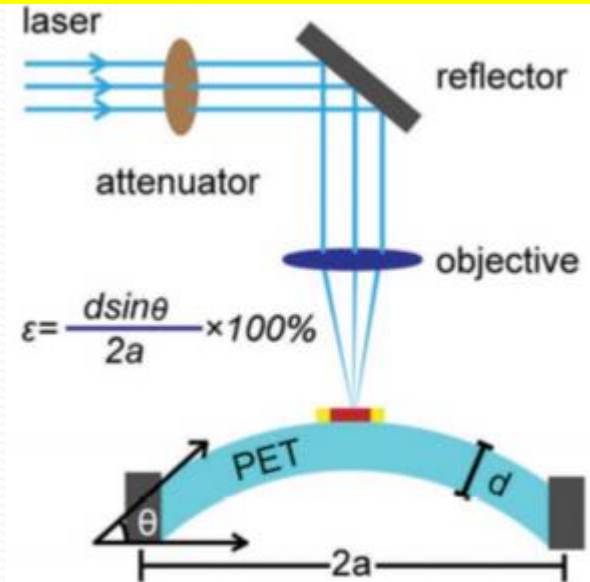
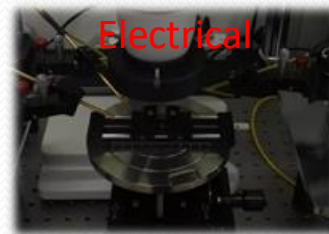
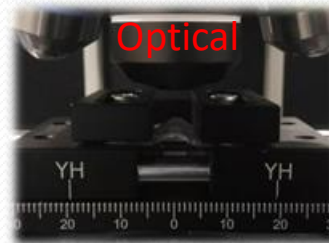
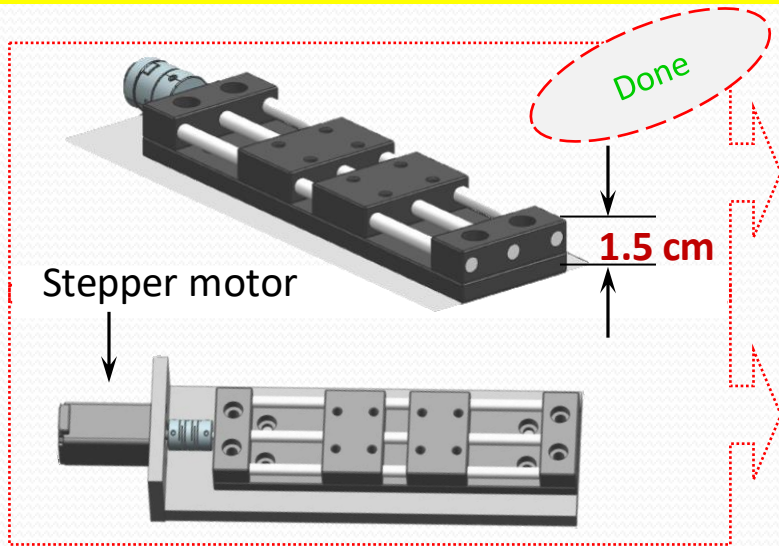
2. Design of flexible field effect transistors (FETs) based on MoS₂

In progress



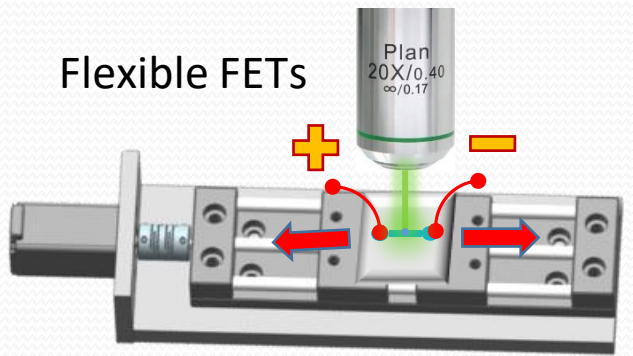
On the schematic description of the device fabrication process shown: **a)** deposition of Au (or transferred graphene monolayer) as a back gate on flexible PET (polyethylene terephthalate) substrate pre-coated PDMS (polydimethylsiloxane); **b)** deposition of oxides (as example, HfO₂ layer) on the substrate; **c)** transferring MoS₂ film on the high-*k* HfO₂ layer; **d)** fabrication of two-terminal MoS₂ device.

3. Development and improvement of a micro-strain system for optoelectrical tests

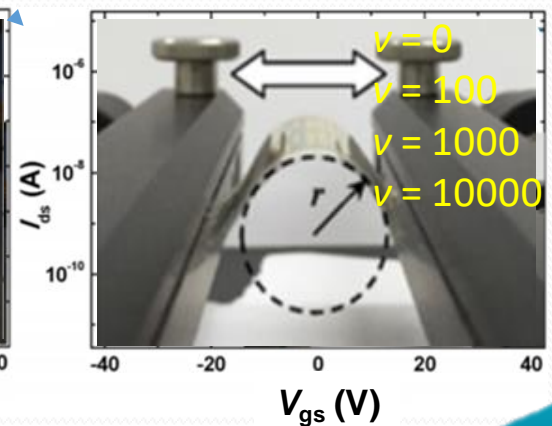
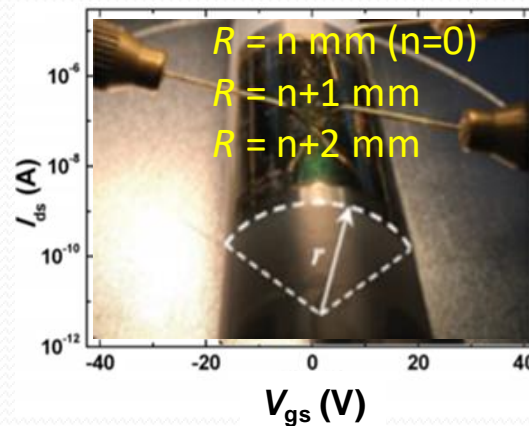


Stretching and compression

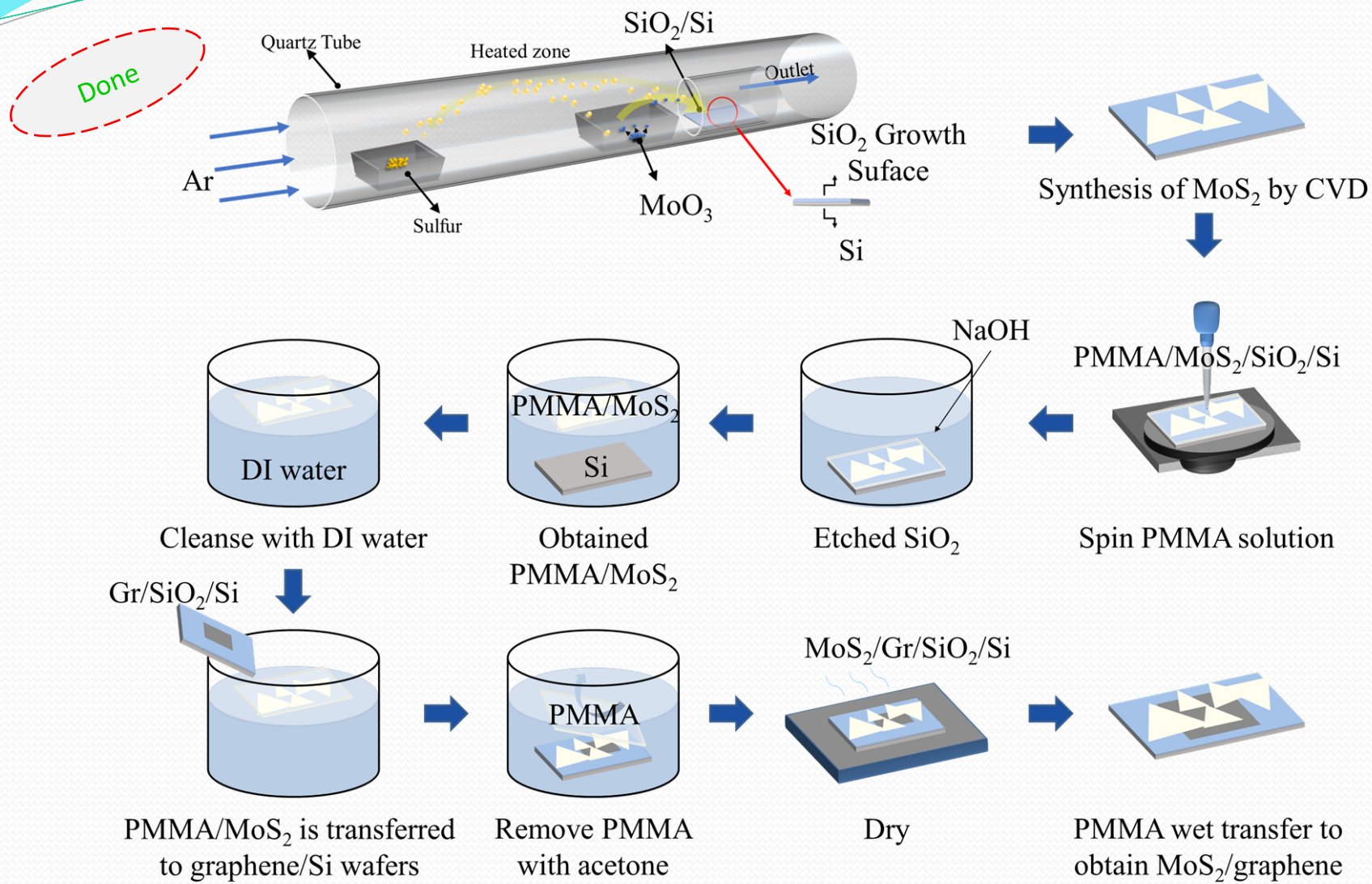
Frequency

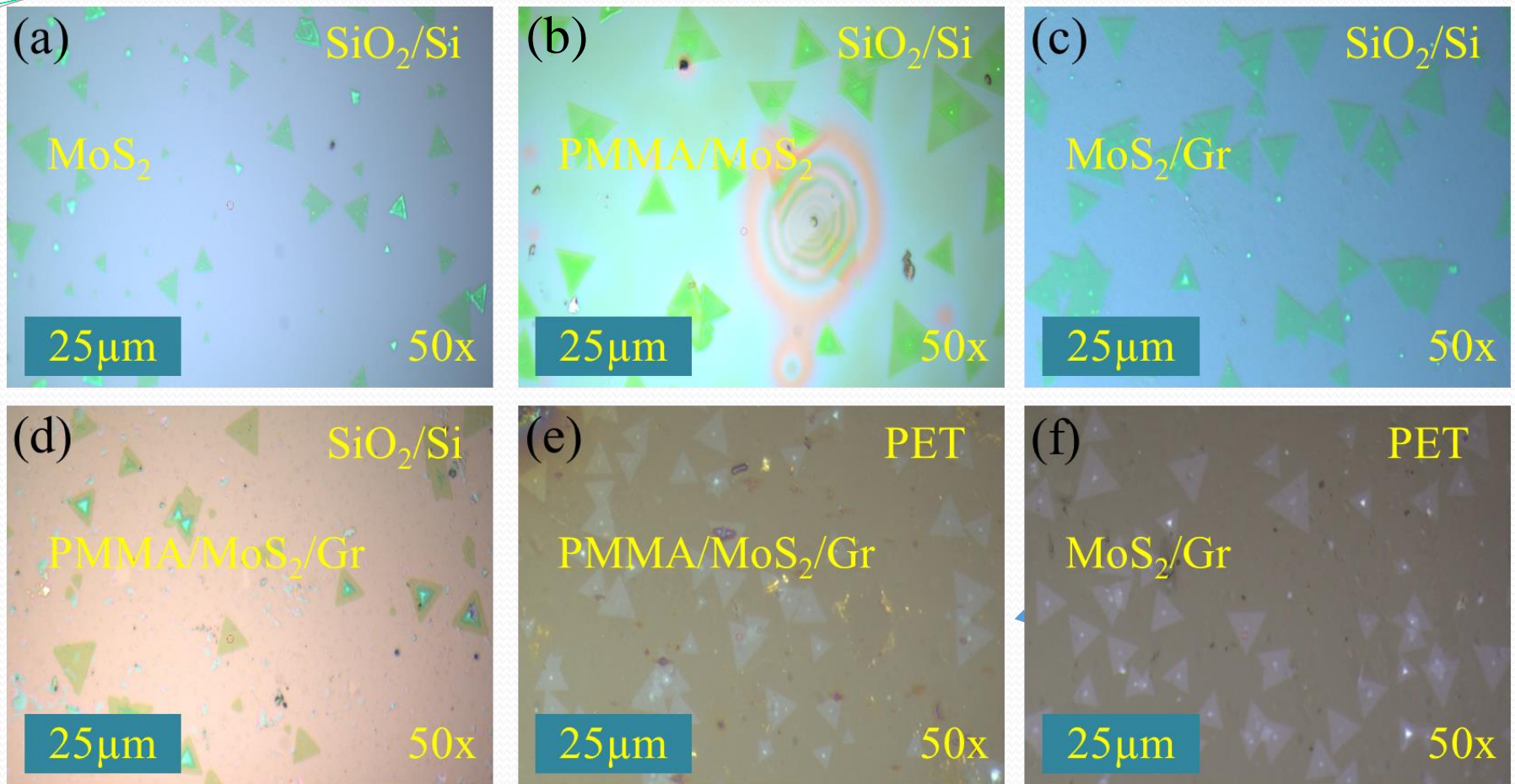


Use of the control strain system for optoelectrical tests



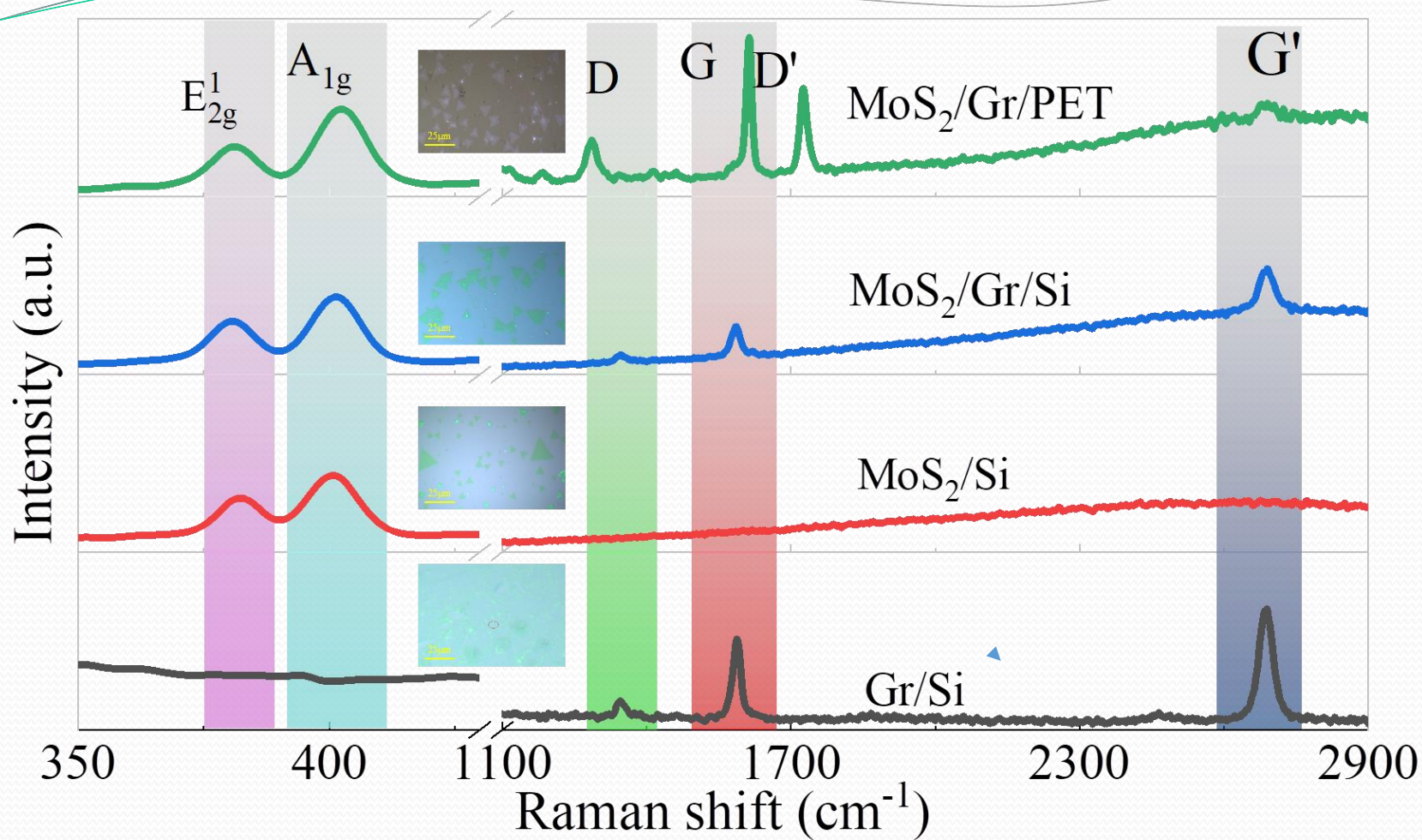
Grown and transfer MoS₂ on the flexible substrates



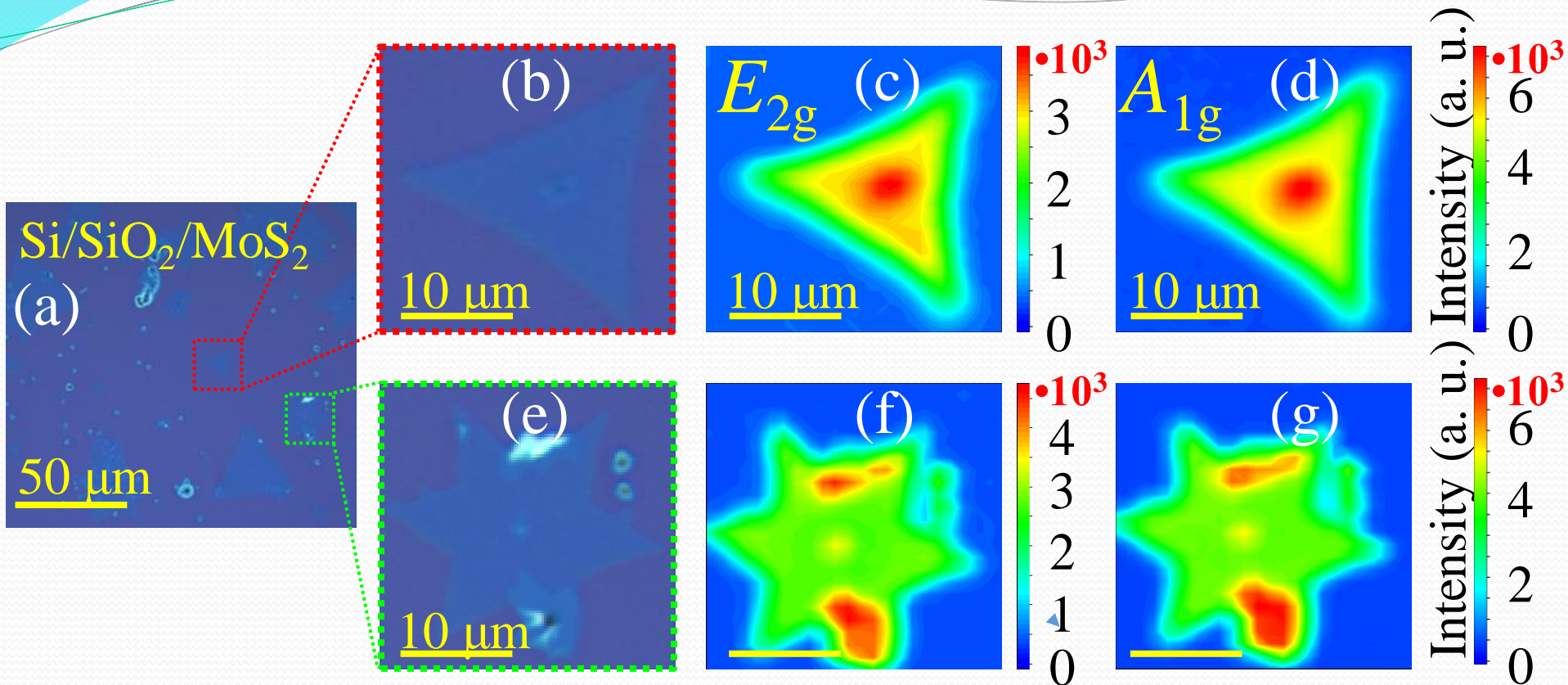


High-quality two-dimensional semiconductors were prepared by chemical vapor deposition (CVD). Optical surface morphology of MoS₂ on Si/SiO₂ (a). MoS₂/Gr is prepared by PMMA transfer and transferred to a flexible substrate (b-f).

Raman spectra



Raman spectra of monolayer-MoS₂/graphene structures on different substrates and precursor ones, as well as their morphology images. $\lambda_{\text{exc}} = 532 \text{ nm}$.



(a) The optical photo of surface MoS₂ flakes grown on SiO₂/Si substrate by CVD method. (b, e) The Raman mapping area of MoS₂ flakes (triangle and star). The mapping of E_{2g} (c, f) and A_{1g} (d, g) bands corresponds to the area in the optical photo.

Raman mapping showed good quality MoS₂ monolayers, but that area is not large and only flakes. We need to continue studying the growth modes to get large monolayers, that are easier to use in flexible electronics.

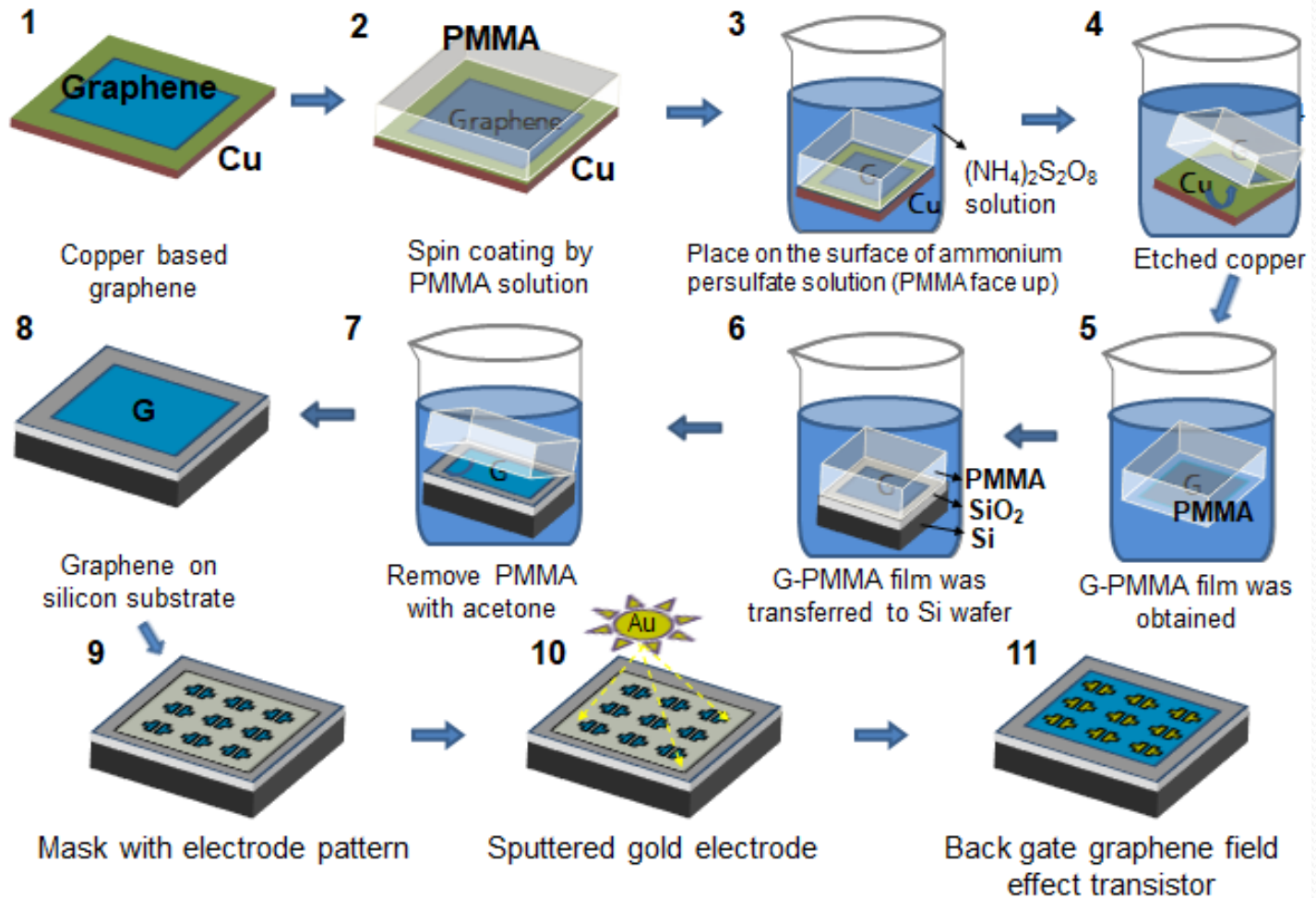
Development Graphene field effect transistors (G-FET)

Done

@Zhu Huiyu

Diagram of transferring monolayer Graphene on a SiO₂/Si substrate.

In progress

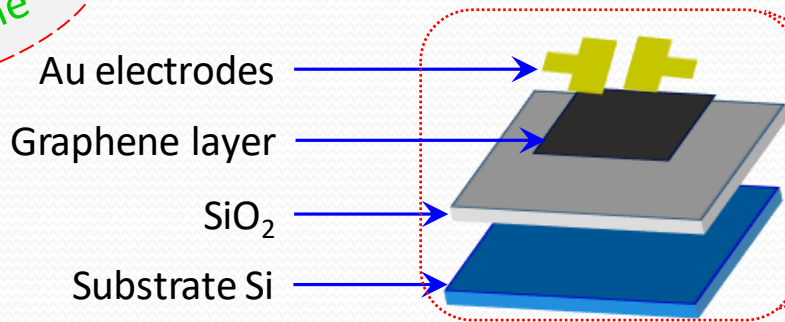


To perform selective detection of Cu⁺ ions, valinomycin (C₅₄H₉₀N₆O₁₈) based ion selective membrane (ISM) with 5 μm nominal thickness will be spin-coated on the entire transferred graphene area and kept at room temperature for 20 minutes for complete solvent volatilization and stable film formation.

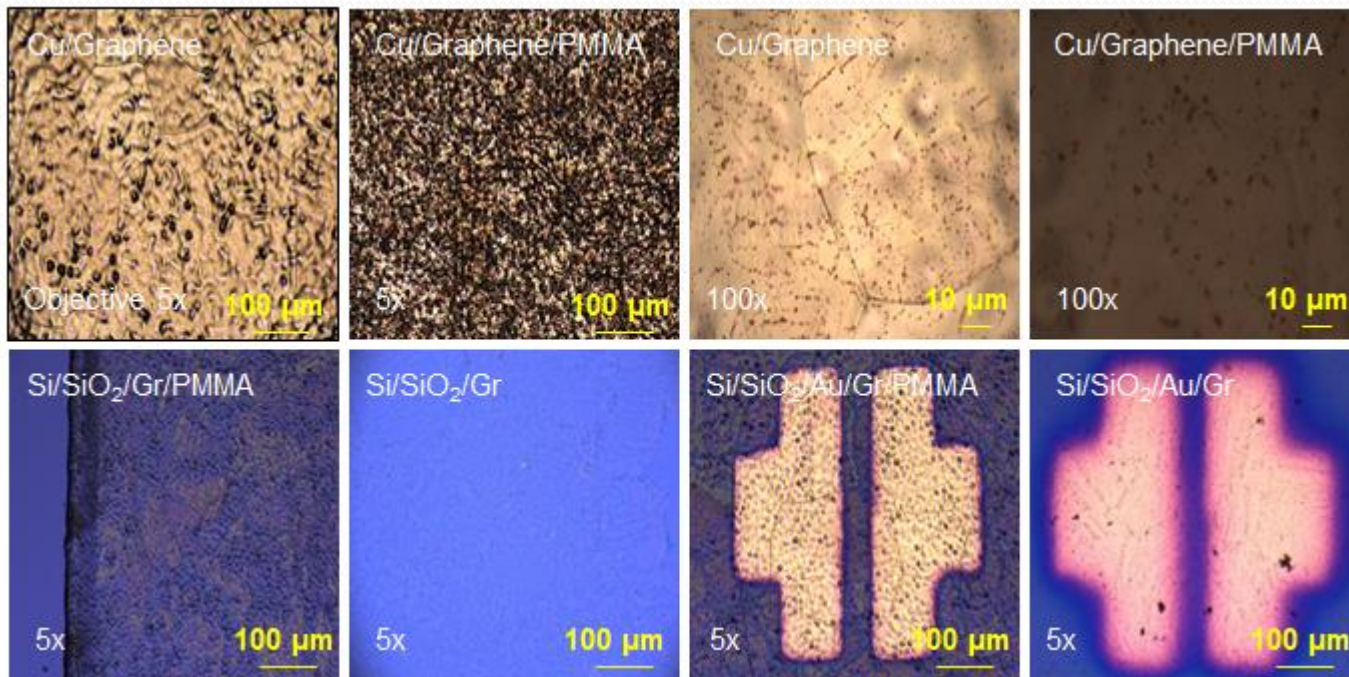
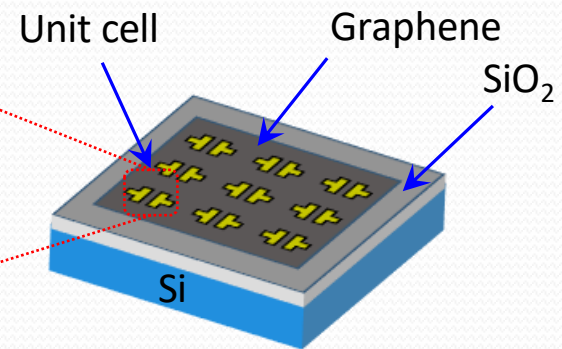
Transferring monolayer on a SiO₂/Si substrate (morphology)

Done

Diagram of sensor unit cell



Back gate graphene field effect transistor



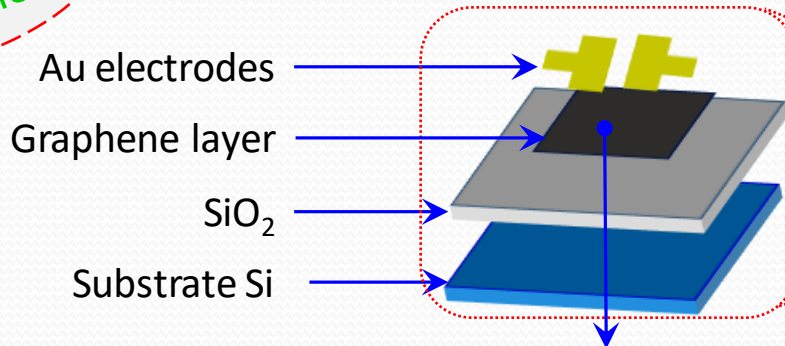
Optical surface morphology of graphene layer on Cu foil and covered by PMMA. Graphene layer transferred to Si/SiO₂ substrate with prepared Au contacts.

@Zhu Huiyu

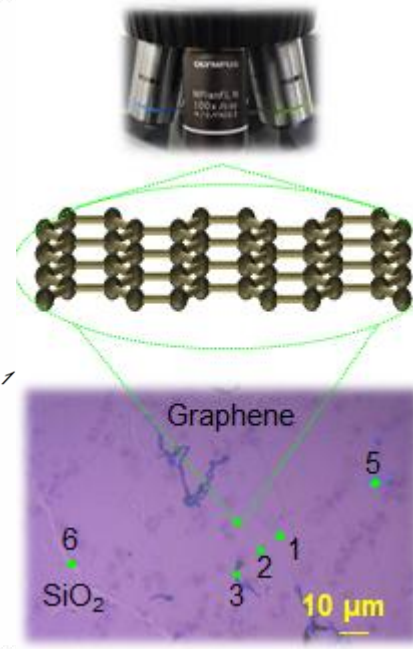
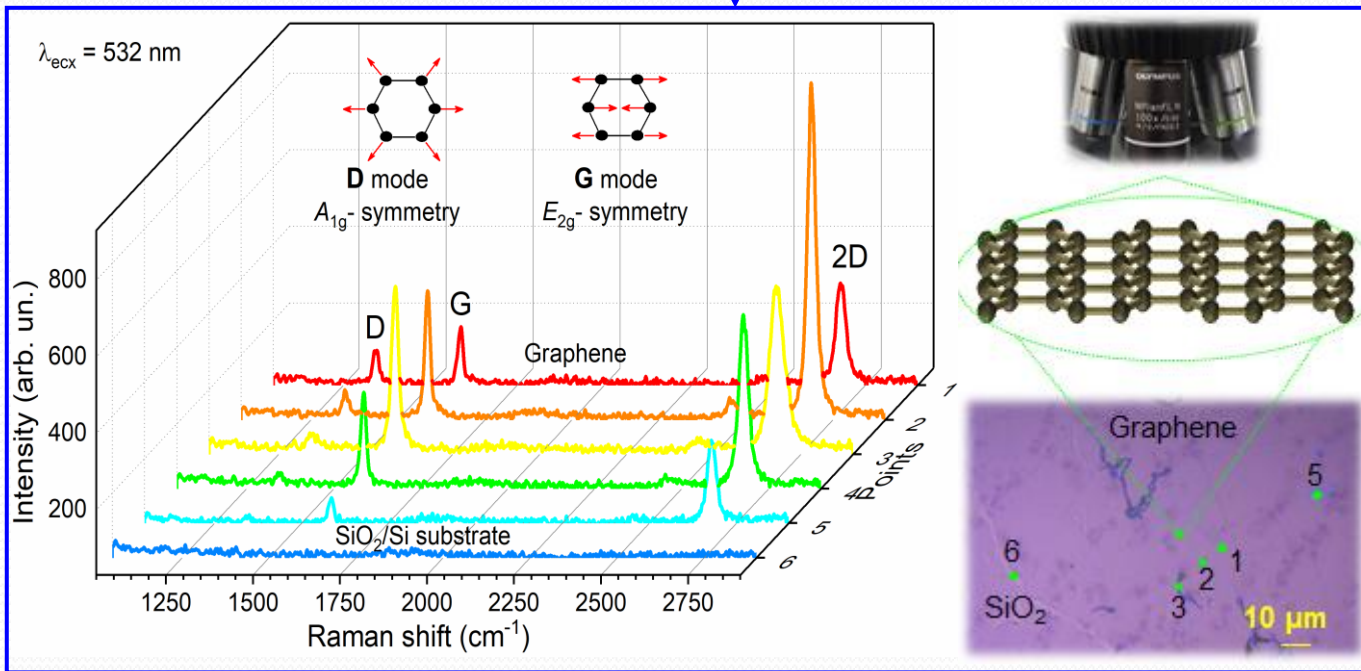
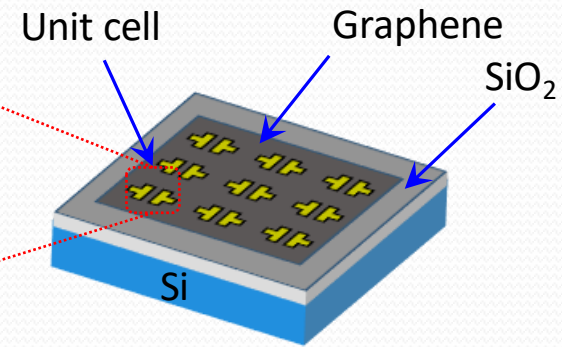
Vibration properties graphene monolayer

Done

Diagram of sensor unit cell



Back gate graphene field effect transistor

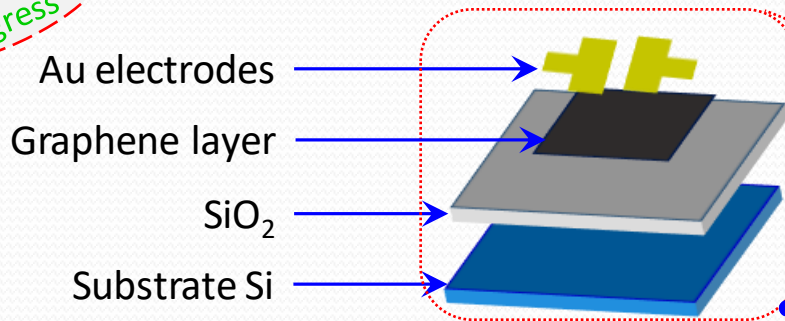


Raman spectra of a graphene monolayer on a Si/SiO₂ substrate at different points on the surface and an image of this layer in the objective lens of an optical microscope.

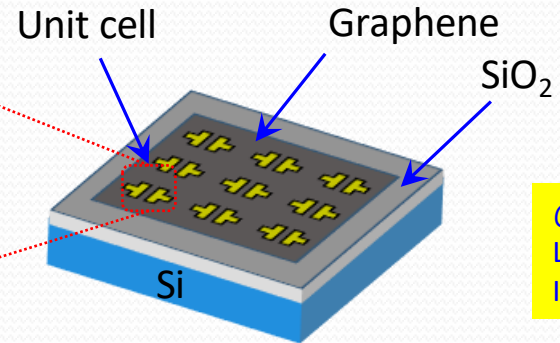
@Zhu Huiyu
Yuhui Qiu
Lin Chubin

Raman vibrational modes of graphene were responsible for the G-, D- and 2D-bands.

Diagram of sensor unit cell



Back gate graphene field effect transistor

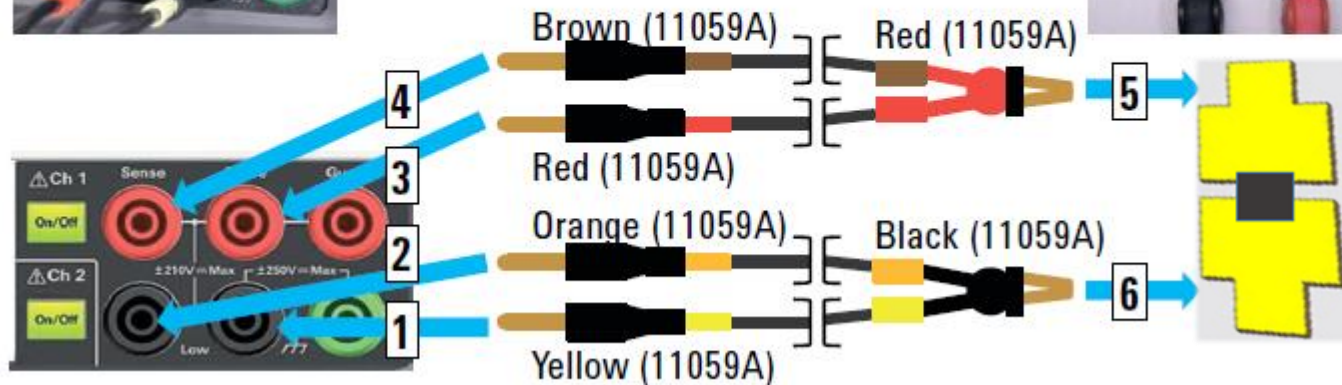


@Zhu Huiyu
Lin Chubin
Ivan

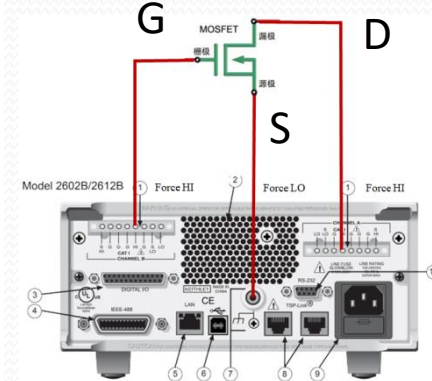
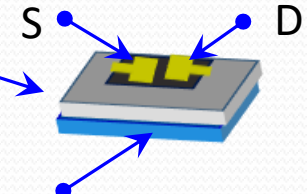
Resistance Measurement Using Keysight 2602B



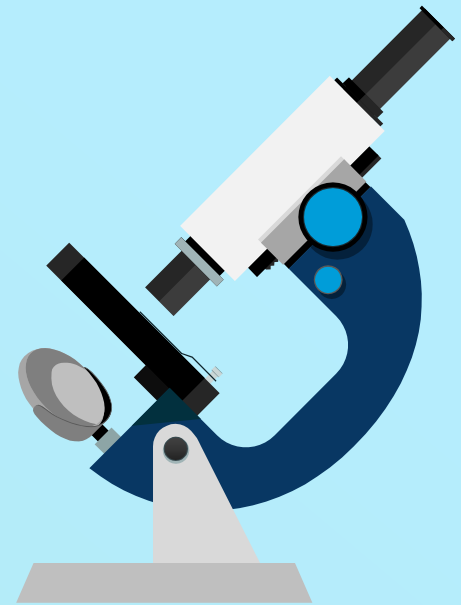
Resistor



Transistor



- 1) 2D materials contribute to developing physical, chemical, bio, and wearable sensors. The large contact surface area in a small volume ratio is one of the key points for this type of 2D-based sensor, achieving a good limit of detection and sensitivity.
 - 2) The mono- and few-layer of MoS_2 flakes (triangles and stars) were grown. Raman spectroscopy was used to get information about the quality of the MoS_2 /graphene structure.
 - 3) MoS_2 flakes were transferred to a flexible substrate to develop a flexible electronic device.
- The growth of a high-quality defect-free MoS_2 monolayer on large areas is still open and will give prospects for implementation in flexible electronics.



Thank you for your consideration!

谢谢

